NSN 5961-01-058-5081

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View Online at https://aerobasegroup.com/nsn/5961-01-058-5081 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To.3 **Electrode Internally-electrically Connected To Case:** Collector **Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Mounting hardware **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 9.0 emitter to base voltage, dc and 400.0 breakdown voltage, collector to emitter, sustained **Current Rating Per Characteristic:** Between 10.00 amperes source cutoff current and 15.00 amperes source cutoff current and 25.00 amperes source cutoff current blank **Power Rating Per Characteristic:** 175.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Test Data Document:** 99971-7541503 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 uninsulated wire lead and 1 case Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: